

Afiq Hamzah

List of Publications by Year in descending order

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Version: 2024-02-01

32
papers

144
citations

1163117
8
h-index

1281871
11
g-index

32
all docs

32
docs citations

32
times ranked

118
citing authors

#	ARTICLE	IF	CITATIONS
1	Device performances analysis of p-type doped silicene-based field effect transistor using SPICE-compatible model. PLoS ONE, 2022, 17, e0264483.	2.5	2
2	Semi-analytical modelling and evaluation of uniformly doped silicene nanotransistors for digital logic gates. PLoS ONE, 2021, 16, e0253289.	2.5	0
3	Performance Analysis of an Efficient Montgomery Multiplier using 7nm FinFET and Junctionless FinFET. , 2021, , .		0
4	A 2 Kbit Memory Array of Mixed-VT GC-eDRAM Implemented in 130nm Standard CMOS Technology. , 2021, , .		0
5	An Efficient March (5n) FSM-Based Memory Built-In Self Test (MBIST) Architecture. , 2021, , .		4
6	Impact of phonon scattering mechanisms on the performance of silicene nanoribbon field-effect transistors. Results in Physics, 2021, 29, 104714.	4.1	7
7	Design of Low Power Gain-Cell eDRAM for 4Kb Memory Array in 130nm CMOS. , 2021, , .		0
8	Electronic properties and carrier transport properties of low-dimensional aluminium doped silicene nanostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 116, 113731.	2.7	11
9	Electronic properties of graphene nanoribbons with line-edge roughness doped with nitrogen and boron. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 117, 113841.	2.7	9
10	Electrical characterization of n-type cylindrical gate all around nanowire junctionless transistor with SiO ₂ and high-k dielectrics. , 2020, , .		3
11	ASIC Implementation and Optimization of 16 Bit SDRAM Memory Controller. , 2020, , .		3
12	Device performance of silicene nanoribbon field-effect transistor under ballistic transport. , 2020, , .		3
13	Carrier transport of rough-edged doped GNR-FETs with metal contacts at various channel widths. Superlattices and Microstructures, 2020, 143, 106548.	3.1	7
14	Reliability Analysis Of Gate-All-Around Floating Gate (GAA-FG) With Variable Oxide Thickness For Flash Memory Cell. , 2020, , .		0
15	A review of the top of the barrier nanotransistor models for semiconductor nanomaterials. Superlattices and Microstructures, 2020, 140, 106429.	3.1	11
16	An Analytical Conductance Model for Gas Detection Based on a Zigzag Carbon Nanotube Sensor. Sensors, 2020, 20, 357.	3.8	4
17	Explicit continuous charge-based compact model of surrounding gate MOSFET (SRGMOSFET) with smooth transition between partially-depleted to fully-depleted operation. Semiconductor Science and Technology, 2020, 35, 045007.	2.0	1
18	Analytical Prediction of Highly Sensitive CNT-FET-Based Sensor Performance for Detection of Gas Molecules. IEEE Access, 2020, 8, 12655-12661.	4.2	9

#	ARTICLE	IF	CITATIONS
19	Carrier statistics of highly doped armchair graphene nanoribbons with edge disorder. Superlattices and Microstructures, 2020, 139, 106404.	3.1	3
20	2D Honeycomb Silicon: A Review on Theoretical Advances for Silicene Field-Effect Transistors. Current Nanoscience, 2020, 16, 595-607.	1.2	12
21	Modeling of lightly-doped drain and source contact with boron and nitrogen in graphene nanoribbon. Chinese Journal of Physics, 2019, 62, 258-273.	3.9	3
22	Effect of low-k oxide thickness variation on gate-all-around floating gate with optimized SiO ₂ /La ₂ O ₃ tunnel barrier. Materials Research Express, 2019, 6, 1150c6.	1.6	0
23	Explicit continuous models of drain current, terminal charges and intrinsic capacitance for a long-channel junctionless nanowire transistor. Physica Scripta, 2019, 94, 105813.	2.5	10
24	Design of 6T SRAM Cell Using Optimized 20 nm SOI Junctionless Transistor. , 2019, , .		3
25	Electronic properties of silicene nanoribbons using tight-binding approach. , 2019, , .		2
26	Graphene as Charge Storage Layer in Floating Gate Flash Memory with Highk Tunnel Barrier Engineering. , 2018, , .		0
27	Low-voltage high-speed programming gate-all-around floating gate memory cell with tunnel barrier engineering. Japanese Journal of Applied Physics, 2018, 57, 06KC02.	1.5	13
28	Band gap engineering of BC 2 N for nanoelectronic applications. Superlattices and Microstructures, 2017, 112, 328-338.	3.1	16
29	Performance prediction of Graphene Nanoscroll and Carbon Nanotube transistors. , 2016, , .		1
30	Explicit continuous charge-based compact model for long channel heavily doped surrounding-gate MOSFETs incorporating interface traps and quantum effects. Semiconductor Science and Technology, 2016, 31, 125020.	2.0	3
31	QUANTUM CAPACITANCE EFFECT ON ZIG-ZAG GRAPHENE NANOSCROLLS (ZGNS) (16, 0). Modern Physics Letters B, 2013, 27, 1350002.	1.9	4
32	Temperature effect on quantum capacitance zig-zag graphene nanoscrolls (ZGNS) (16,0). , 2012, , .		0